

November 2013

#### **FCI7N60**

## N-Channel SuperFET<sup>®</sup> MOSFET 600 V, 7 A, 600 m $\Omega$

#### **Features**

- 650V @ T<sub>J</sub> = 150°C
- Typ.  $R_{DS(on)}$  = 530 m $\Omega$
- Ultra Low Gate Charge (Typ.  $Q_g$  = 23 nC)
- Low Effective Output Capacitance (Typ. C<sub>oss(eff.)</sub> = 60 pF)
- · 100% Avalanche Tested
- · RoHS compliant

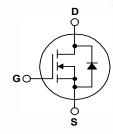
#### **Application**

- Lighting
- · Solar Inverter
- · AC-DC Power Supply

#### **Description**

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.





#### **MOSFET Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter	FCI7N60	Unit
$V_{DSS}$	Drain to Source Voltage		600	V
	Drain Current	- Continuous (T <sub>C</sub> = 25°C)	7	А
ID	Dialii Cuitent	- Continuous (T <sub>C</sub> = 100°C)	4.4	A
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	21	Α
$V_{GSS}$	Gate to Source Voltage		±30	V
E <sub>AS</sub>	Single Pulsed Avalanche Ene	rgy (Note 2)	230	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	7	А
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		8.3	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
В	Power Dissipation	(T <sub>C</sub> = 25°C)	83	W
$P_{D}$	Fower Dissipation	- Derate Above 25°C	0.67	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
$T_L$	Maximum Lead Temperature	for Soldering, 1/8" from Case for 5 Seconds	300	°C

#### **Thermal Characteristics**

Symbol	Parameter	FCI7N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	°C/W

#### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCI7N60	FCI7N60	I <sup>2</sup> -PAK	Tube	N/A	N/A	50 units

#### **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub> Drain to Source Breakdown Voltage	Drain to Course Progledown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_C = 25^{\circ}\text{C}$	600	-	-	V
	Drain to Source Breakdown voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_C = 150^{\circ}\text{C}$	-	650	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 μA, Referenced to 25°C	-	0.6	-	V/°C
BV <sub>DS</sub>	Drain-Source Avalanche Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 7 A	-	700	-	V
	Zoro Coto Voltago Droin Current	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	-	-	1	^
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 480 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V	-	-	±100	nA

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 3.5 \text{ A}$	-	0.53	0.6	Ω
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 3.5 \text{ A}$	-	6	1	S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V - 25 V V - 0 V	-	710	920	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		380	500	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1.0 WH12	-	34	-	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	22	29	pF
C <sub>oss(eff.)</sub>	Effective Output Capacitance	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V	-	60	-	pF

#### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	35	80	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 300 \text{ V}, I_D = 7 \text{ A},$	-	55	120	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10 \text{ V, R}_{G} = 25 \Omega$		75	160	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	-	32	75	ns
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>DS</sub> = 480 V, I <sub>D</sub> = 7 A,	/-	23	30	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	V <sub>GS</sub> = 10 V	/ -	4.2	5.5	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(Note 4)	-	11.5	-	nC

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current			-	7	Α
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	21	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 7 A	-	-	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 7 A,	-	360	// <b>-</b>	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{GS} = 0 \text{ V, } I_{SD} = 7 \text{ A,}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	4.5	-	μC

#### Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. I $_{AS}$  = 3.5 A, V $_{DD}$  = 50 V, R $_{G}$  = 25 $\Omega$ , starting T $_{J}$  = 25 $^{\circ}$ C.
- 3. I  $_{SD} \le 7$  A, di/dt  $\le 200$  A/µs, V  $_{DD} \le BV _{DSS}$ , starting T  $_{J}$  = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

#### **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

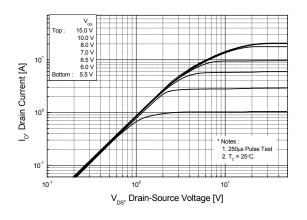


Figure 2. Transfer Characteristics

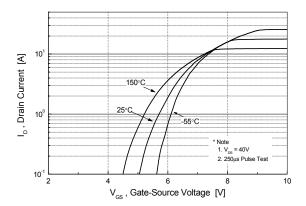


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

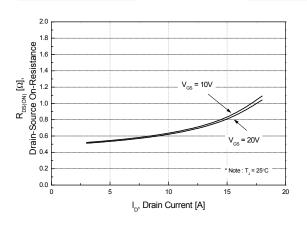


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

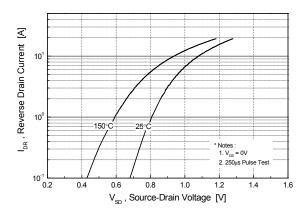


Figure 5. Capacitance Characteristics

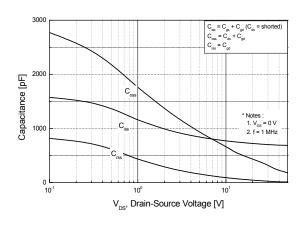
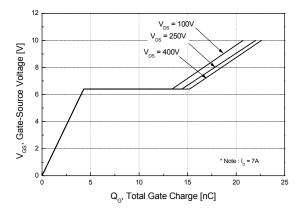


Figure 6. Gate Charge Characteristics



#### Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

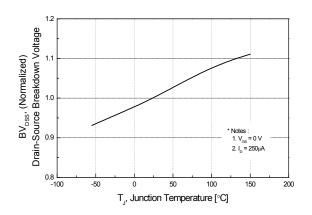


Figure 8. On-Resistance Variation vs. Temperature

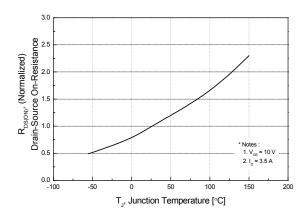


Figure 9. Maximum Safe Operating Area

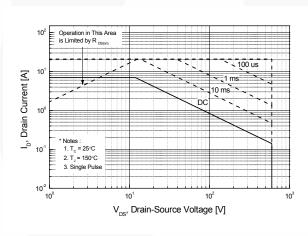


Figure 10. Maximum Drain Current vs. Case Temperature

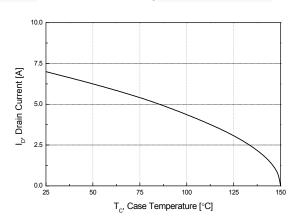
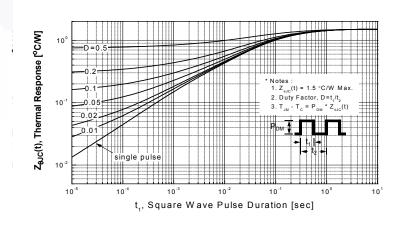


Figure 11. Transient Thermal Response Curve



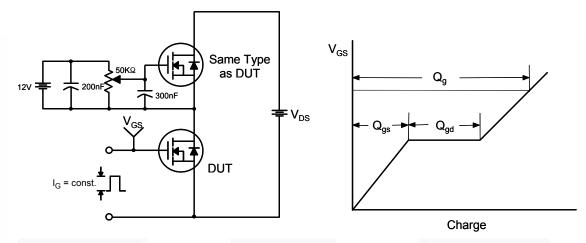


Figure 12. Gate Charge Test Circuit & Waveform

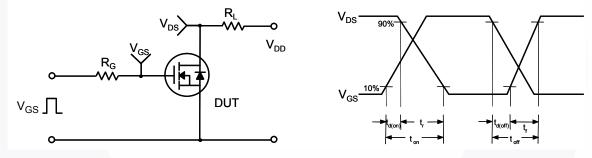


Figure 13. Resistive Switching Test Circuit & Waveforms

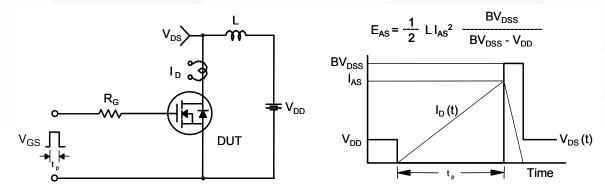


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

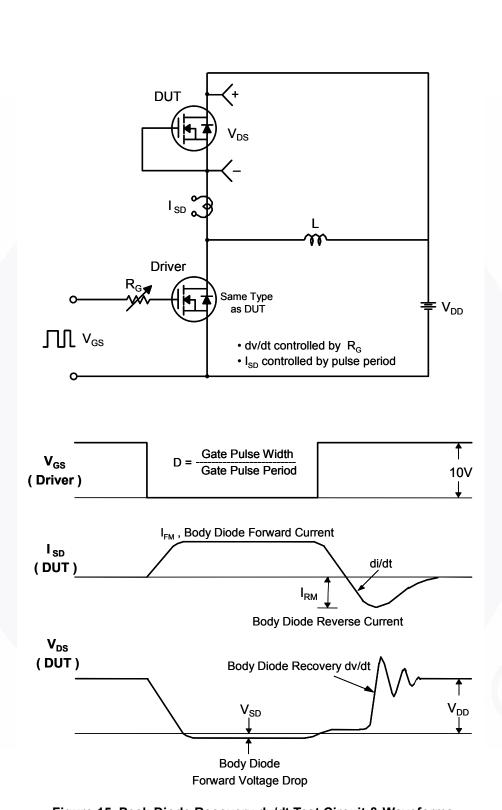


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

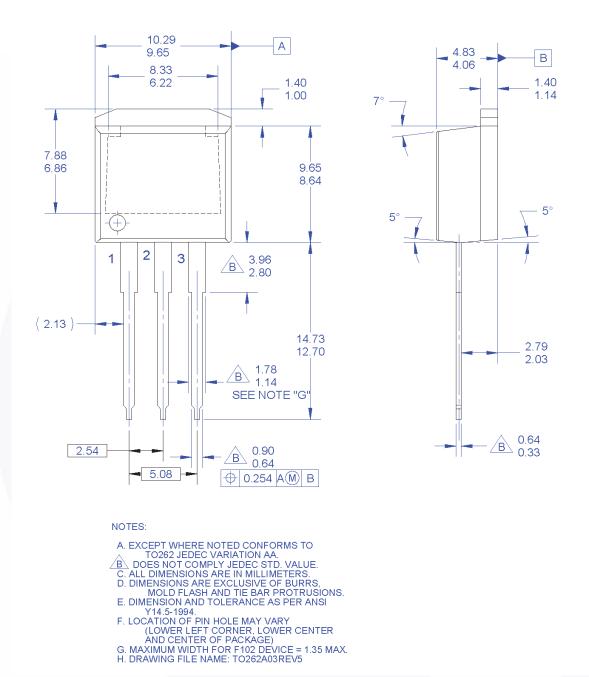


Figure 16. TO262 (I<sup>2</sup>PAK), Molded, 3-Lead, Jedec Variation AA

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TT262-003





#### **TRADEMARKS**

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™ AX-CAP® BitSiC™ Build it Now™ CorePLUS™ CorePOWER™  $CROSSVOLT^{\text{TM}}$ 

CTI ™ Current Transfer Logic™ DEUXPEED® Dual Cool™

EcoSPARK® EfficentMax™ ESBC™

Fairchild<sup>®</sup> Fairchild Semiconductor® FACT Quiet Series™

FACT® FAST® FastvCore™ FETBench™ FPS™

F-PFS™ FRFET®

Global Power Resource<sup>SM</sup> GreenBridge™ Green FPS™

Green FPS™ e-Series™

G*max*™ GTO™ IntelliMAX™ ISOPLANAR™

Marking Small Speakers Sound Louder

and Better™ MegaBuck™ MICROCOUPLER™ MicroFET™ MicroPak™

MicroPak2™ MillerDrive™ MotionMax™ mWSaver® OptoHiT™ OPTOLOGIC® OPTOPLANAR® PowerTrench® PowerXS™

Programmable Active Droop™

**QFET** QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SignalWise™

SmartMax™ SMART START™

Solutions for Your Success™

STEALTH™

SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SvncFET™

SYSTEM ®\* TinyBoost<sup>®</sup> TinyBuck<sup>®</sup> TinyCalc™ TinvLogic<sup>®</sup> TINYOPTO™ TinvPower™ TinyPWM™

Sync-Lock™

TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®\* uSerDes™

UHC<sup>®</sup> Ultra FRFET™ UniFFT™ VCX™ VisualMax™ VoltagePlus™ XSTM

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY
FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE
EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev 166

# AMEYA360 Components Supply Platform

#### **Authorized Distribution Brand:**

























#### Website:

Welcome to visit www.ameya360.com

#### Contact Us:

#### > Address:

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

#### > Sales:

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

#### Customer Service :

Email service@ameya360.com

### Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com